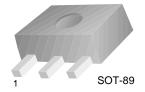


### **KSB1121**

### **High Current Driver Applications**

- Low Collector-Emitter Saturation Voltage
- Large Current Capacity and Wide SOA
- Fast Switching Speed
- Complement to KSD1621



1. Base 2. Collector 3. Emitter

## **PNP Epitaxial Planar Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	-30	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current	-2	Α
	Collector Power Dissipation	500	mW
P <sub>C</sub> P <sub>C</sub> *		1.3	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> Mounted on Ceramic Board (250mm2 x 0.8mm)

## $\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} = 25 ^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}$ = -10 $\mu$ A, $I_{E}$ = 0	-30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -1 \text{mA}, I_B = 0$	-25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -20V, I_{E} = 0$			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -4V, I_{C} = 0$			-100	nA
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> = -2V, I <sub>C</sub> = -0.1A	100		560	
$h_{FE2}$		$V_{CE} = -2V, I_{C} = -1.5A$	65			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1.5A, I <sub>B</sub> = -75mA		-0.35	-0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1.5A, I <sub>B</sub> = -75mA		-0.85	-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -10V, I_{C} = -50mA$		150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz		32		pF
t <sub>ON</sub>	* Turn On Time	$V_{CC} = -12V, V_{BE} = -5V$		60		ns
t <sub>STG</sub>	* Storage Time	$I_{B1} = -I_{B2} = -25 \text{mA}$		350		ns
t <sub>F</sub>	* Fall time	$I_C$ = -500mA, $R_L$ =24 $\Omega$		25		ns

<sup>\*</sup> Pulse Test: PW≤20μs, Duty Cycle≤1%

## $h_{\text{FE}}$ Classification

Classification	R	S	Т	U
h <sub>FE1</sub>	100 ~ 200	140 ~ 280	200 ~ 400	280 ~ 560



SZX

 $h_{\text{FE}}$  Grade

# **Typical Characteristics**

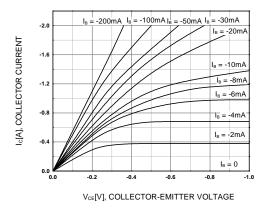


Figure 1. Static Characteristic

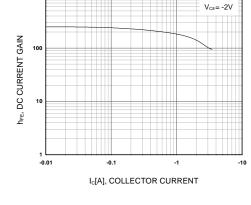


Figure 2. DC current Gain

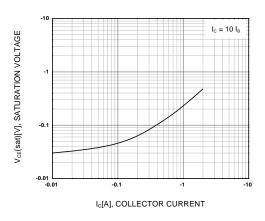


Figure 3. Collector-Emitter Saturation Voltage

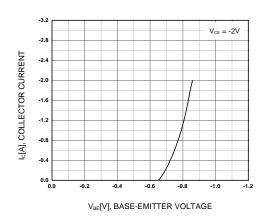


Figure 4. Base-Emitter On Voltage

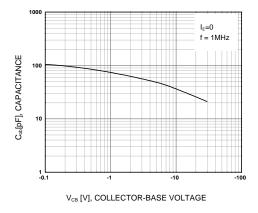


Figure 5. Collector Output Capacitance

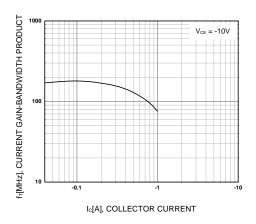
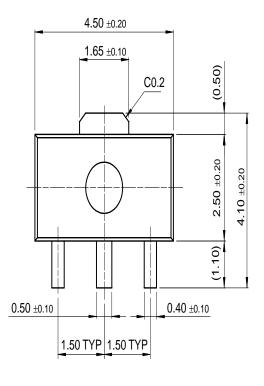


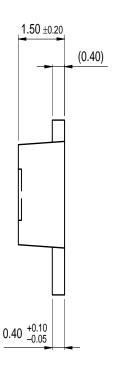
Figure 6. Current Gain Bandwidth Product

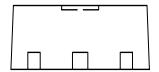
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# **Package Demensions**

# **SOT-89**







Dimensions in Millimeters

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